



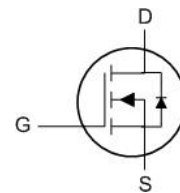
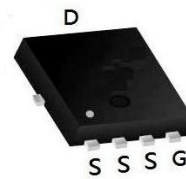
- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

BVDSS	RDSON	ID
30V	3.5mΩ	100A

Description

The XXW100N03D is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The XXW100N03D meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN3X3 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	±20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	100		A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50		A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	19	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	16	A
I_{DM}	Pulsed Drain Current ²	162		A
EAS	Single Pulse Avalanche Energy ³	144.7		mJ
I_{AS}	Avalanche Current	53.8		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	62.5		W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	6	2.42	W
T_{STG}	Storage Temperature Range	-55 to 175		°C
T_J	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	25	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.4	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=30A$	-	3.5	4.7	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	6.0	10	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	2100	-	pF
C_{oss}	Output Capacitance		-	326	-	pF
C_{rss}	Reverse Transfer Capacitance		-	282	-	pF
Q_g	Total Gate Charge	$V_{DS}=15V, I_D=30A,$ $V_{GS}=10V$	-	45	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	15	-	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=15V,$ $I_D=30A, R_{GEN}=3\Omega,$ $V_{GS}=10V$	-	21	-	ns
t_r	Turn-on Rise Time		-	32	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	59	-	ns
t_f	Turn-off Fall Time		-	34	-	ns
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20A, di/dt=100A/\mu s$	-	15	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: $T_J=25^{\circ}\text{C}, V_G=10V, R_G=25\Omega, L=0.5\text{mH}, I_{AS}=18.4A$

3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

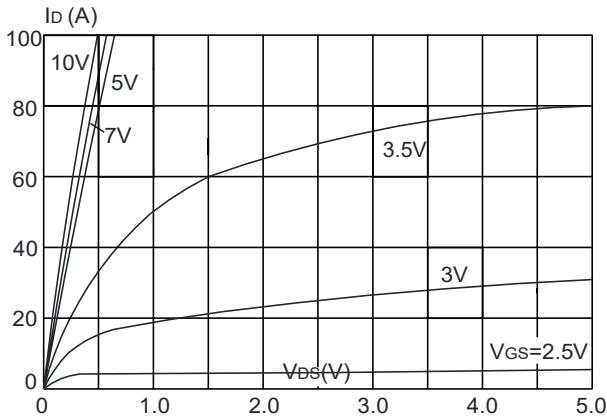
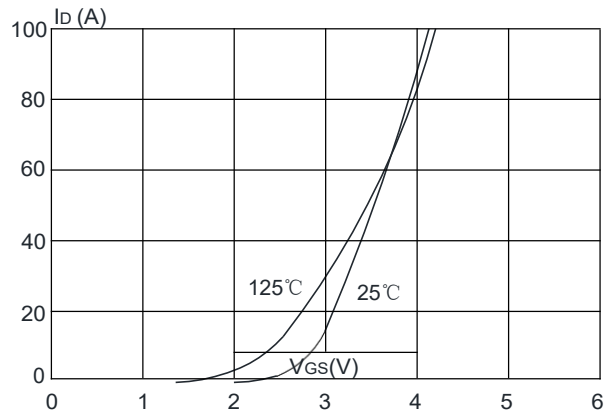
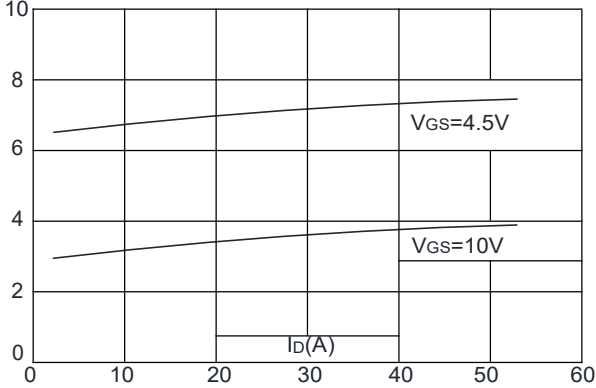
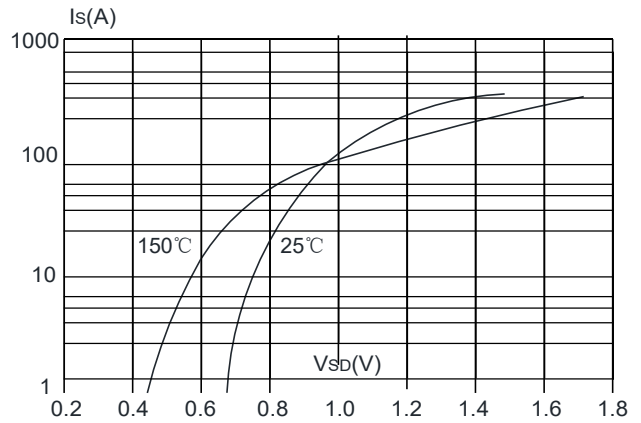
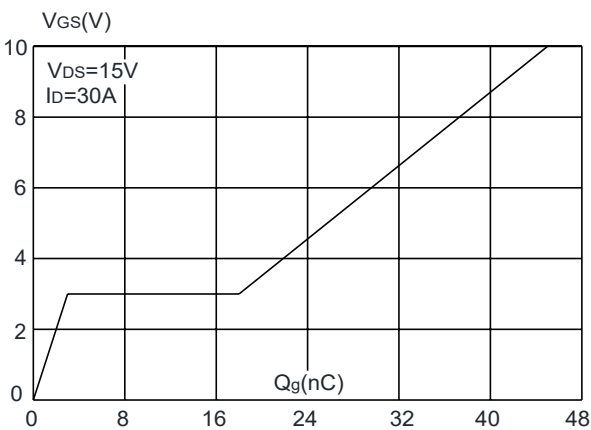
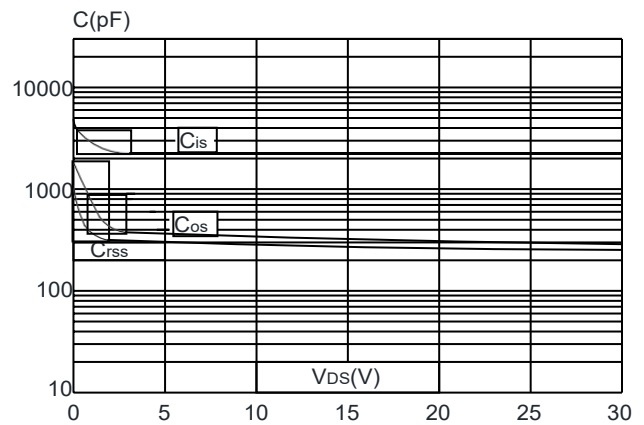
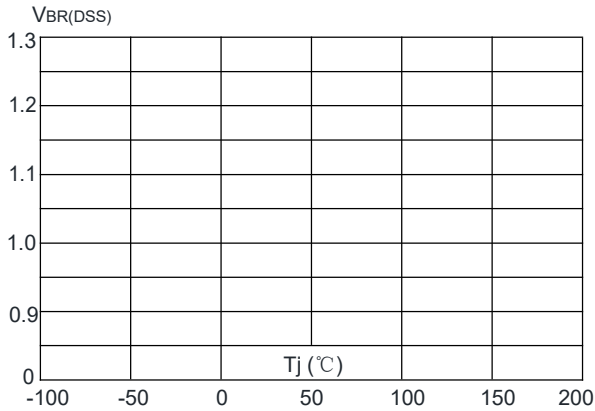
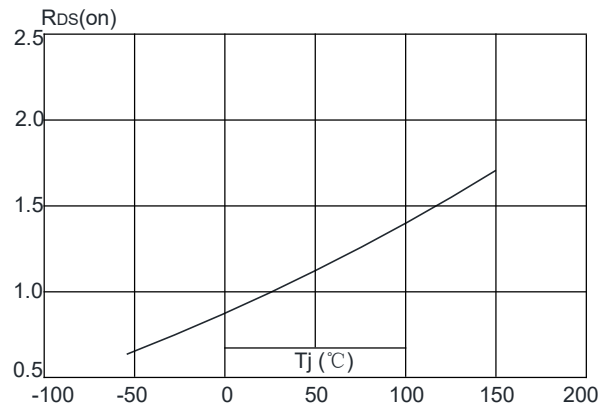
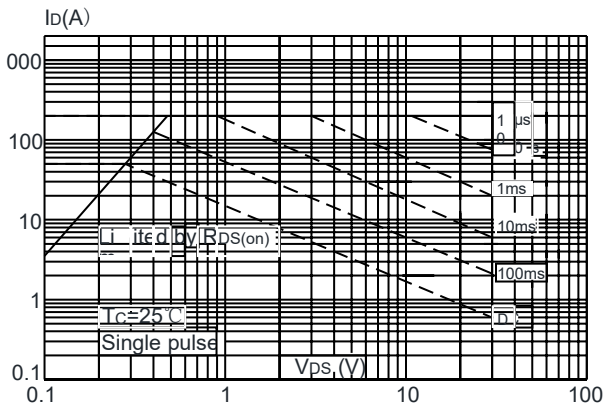
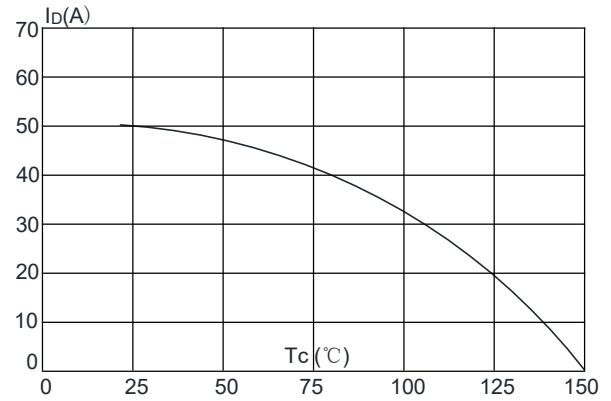
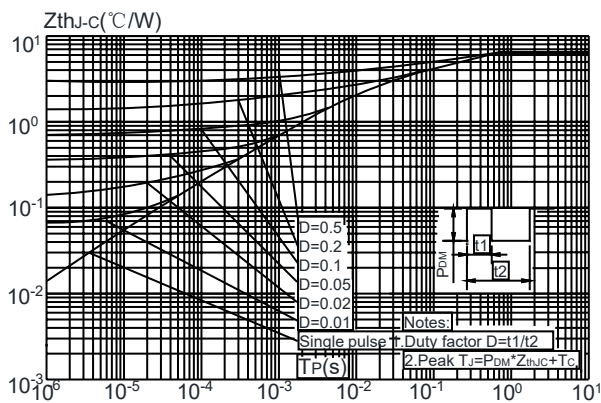
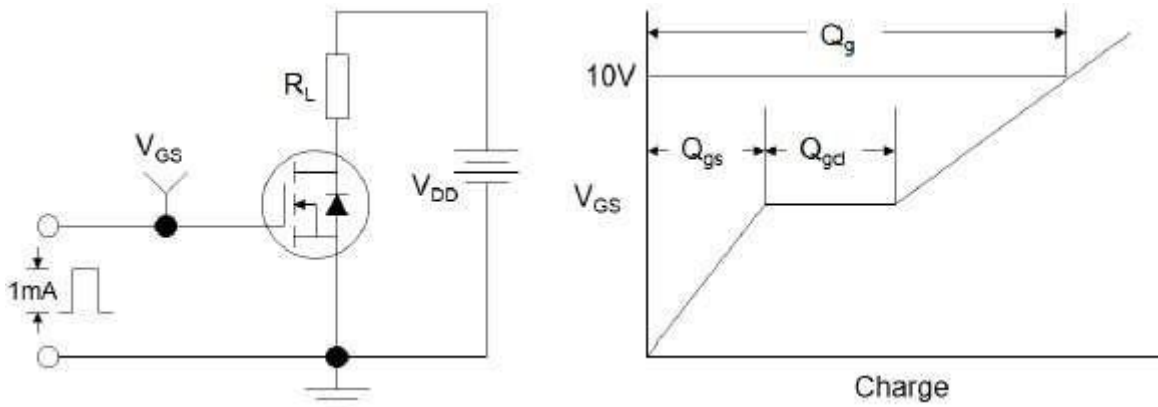
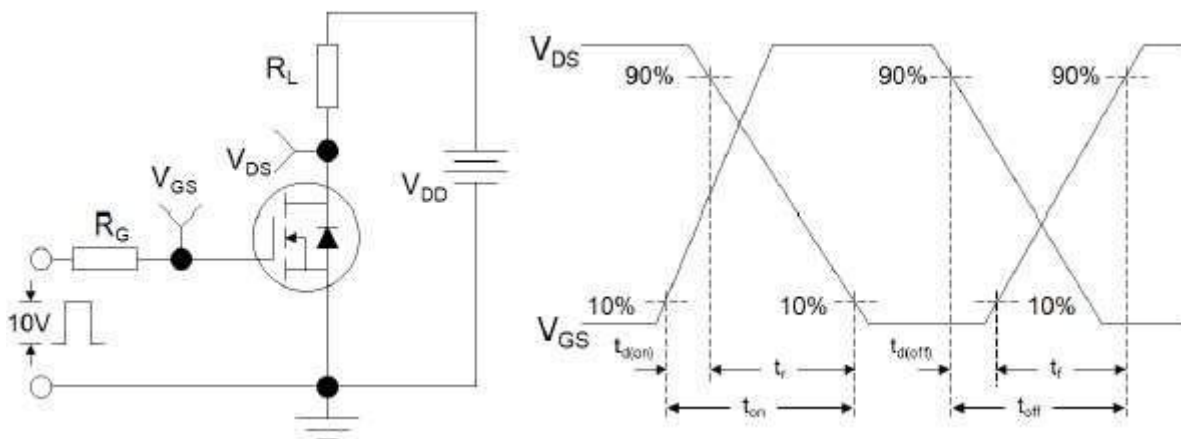
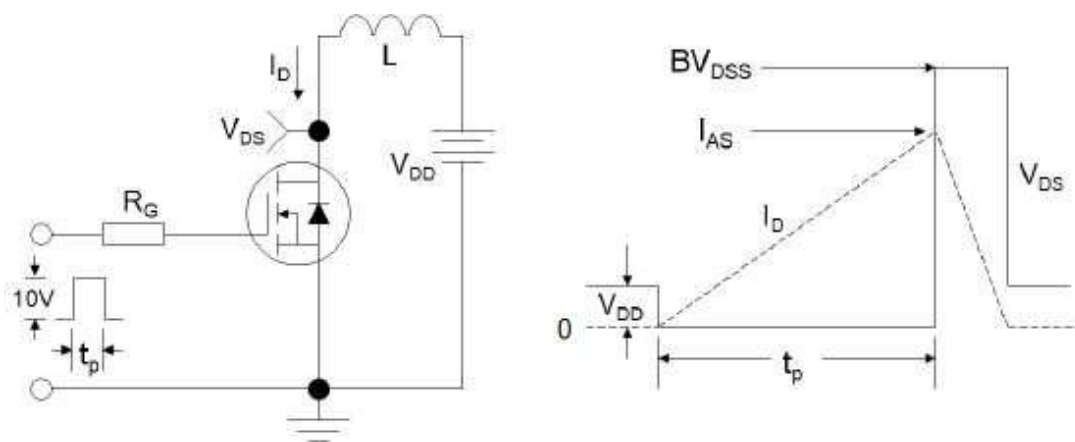
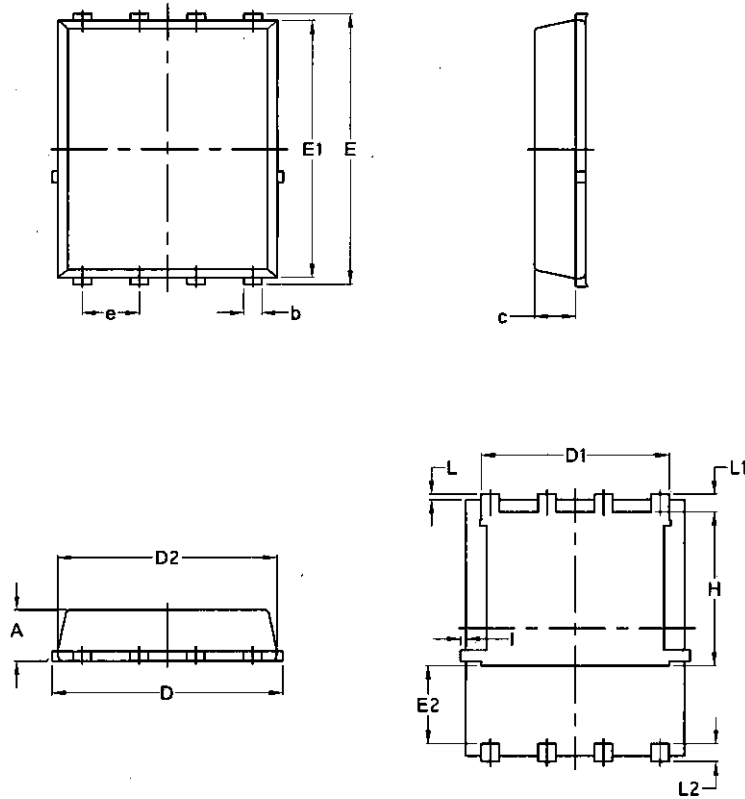
Figure 1: Output Characteristics

Figure 2: Typical Transfer Characteristics

Figure 3: On-resistance vs. Drain Current

Figure 4: Body Diode Characteristics

Figure 5: Gate Charge Characteristics

Figure 6: Capacitance Characteristics


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

Figure 8: Normalized on Resistance vs. Junction Temperature

Figure 9: Maximum Safe Operating Area

Figure 10: Maximum Continuous Drain Current vs. Case Temperature

Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (PDFN3.3*3.3-8L)


Test Circuit

Figure1:Gate Charge Test Circuit & Waveform

Figure 2: Resistive Switching Test Circuit & Waveforms

Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

Package Mechanical Data-PDFN3*3-8L-JQ Single

COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		